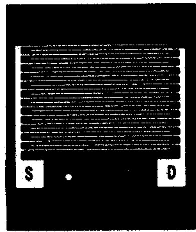
N-CHANNEL JUNCTION FET

CHIP NUMBER FN9



.030" (0.762mm)

.027" (0.686mm)

Die Size: 27 x 30 (mils)
0.686 x .0.762(mm)
4 x 4 (mils)
Pad Size: 0.102 x 0.102(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the die be eutectically mounted with gold silicon preform 98/2%.

b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV_{GSS}	-25	-30	-45	V	V_{DS} = 0, I_G = 1μA
I_{DSS}	100	400	700	mA	V_{DS} = 5V, V_{GS} = 0 (pulse test)
g_{fs}		10		mmho	V_{DG} = 10V, I_D, = 2mA
I_{GSS}		-50	-500	pA	V_{GS} =-15V, V_{DS} = 0
r_{DS}	4.5	6.0	20	Ω	V_{DS} = 100mV, V_{GS} = 0
$V_{GS(off)}$	-0.5	5.0	12.0	V	V_{DS} = 5V, I_D = 3nA
C_{rss}		12	20	pF	V_{DG} = 10V, V_{DG} = 0, f = 1MHz
C_{iss}		25	35	pF	V_{SG} = 10V, V_{DS} = 0, f = 1MHz
$\bar{e}_n$		5.0		nV/√Hz	V_{DG} = 15V, I_D = 2mA, f = 10Hz

TYPICAL DEVICE TYPES: 2N5432 - 2N5434, SDF1000 series

CHIP TYPE FN9